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List of Publications by Year
in descending order

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16	143	1307594	1199594
papers	citations	7 h-index	12 g-index

16	16	16	163
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	An Efficient, Broadband SiGe HBT Non-Uniform Distributed Power Amplifier Leveraging a Compact, Two-Section Î»/4 Output Impedance Transformer. IEEE Transactions on Microwave Theory and Techniques, 2022, 70, 3524-3533.	4.6	4
2	A Compact, Low Loss, and Broadband Two-Section Lumped-Element Wilkinson Power Combiner Using 130 nm SiGe HBT BiCMOS Technology. , 2022, , .		0
3	A New Emitter-Base-Collector-Base-Emitter SiGe HBT for High Power, Single-Pole Double-Throw X-Band Switches. IEEE Electron Device Letters, 2021, 42, 465-468.	3.9	4
4	A 2â€“24 GHz SiGe HBT Cascode Non-uniform Distributed Power Amplifier Using A Compact, Wideband Two-Section Lumped Element Output Impedance Transformer. , 2021, , .		4
5	Highly Linear High-Power 802.11ac/ax WLAN SiGe HBT Power Amplifiers With a Compact 2nd-Harmonic-Shorted Four-Way Transformer and a Thermally Compensating Dynamic Bias Circuit. IEEE Journal of Solid-State Circuits, 2020, 55, 2356-2370.	5.4	26
6	A Highly Efficient X-Band Inverse Class-F SiGe HBT Cascode Power Amplifier With Harmonic-Tuned Wilkinson Power Combiner. IEEE Transactions on Circuits and Systems II: Express Briefs, 2018, 65, 1609-1613.	3.0	16
7	A Compact Highly Efficient High-Power Ka-band SiGe HBT Cascode Frequency Doubler With Four-Way Input Transformer Balun. IEEE Transactions on Microwave Theory and Techniques, 2018, 66, 2879-2887.	4.6	19
8	On the Application of Inverse-Mode SiGe HBTs in RF Receivers for the Mitigation of Single-Event Transients. IEEE Transactions on Nuclear Science, 2017, 64, 1142-1150.	2.0	9
9	An X-band inverse class-F SiGe HBT cascode power amplifier With harmonic-tuned output transformer. , 2017, , .		12
10	A Compact, Wideband Lumped-Element Wilkinson Power Divider/Combiner Using Symmetric Inductors with Embedded Capacitors. IEEE Microwave and Wireless Components Letters, 2016, 26, 595-597.	3.2	19
11	Inverse classâ€‹<scp>F</scp><scp>X</scp>â€band <scp>S</scp>i<scp>G</scp>e <scp>HBT</scp> power amplifier with 44% <scp>PAE</scp> and 24.5 d<scp>B</scp>m peak output power. Microwave and Optical Technology Letters, 2016, 58, 2868-2871.	1.4	1
12	Co-design of a SiGe BiCMOS X-band, asymmetric, low insertion loss, high power handling SPDT Switch and an Ultra Low Noise LNA for next-generation T/R modules. , 2016, , .		3
13	A Compact, Active SiGe Power Divider With Multi-Octave Bandwidth. IEEE Microwave and Wireless Components Letters, 2016, 26, 945-947.	3.2	6
14	Advantages of utilizing throughâ€‹siliconâ€vias in <scp>SiGe</scp> HBT RF lowâ€noise amplifier design. Microwave and Optical Technology Letters, 2015, 57, 2703-2706.	1.4	1
15	High-Power GaN-Based Light-Emitting Diodes Using Thermally Stable and Highly Reflective Nano-Scaled Niâ€“Agâ€“Niâ€“Au Mirror. IEEE Photonics Technology Letters, 2011, 23, 1685-1687.	2.5	11
16	V-Band Beam-Steering ASK Transmitter and Receiver Using BCB-Based System-on-Package Technology on Silicon Mother Board. IEEE Microwave and Wireless Components Letters, 2011, 21, 619-621.	3.2	8